

isc Silicon PNP Power Transistor

2SB921

DESCRIPTION

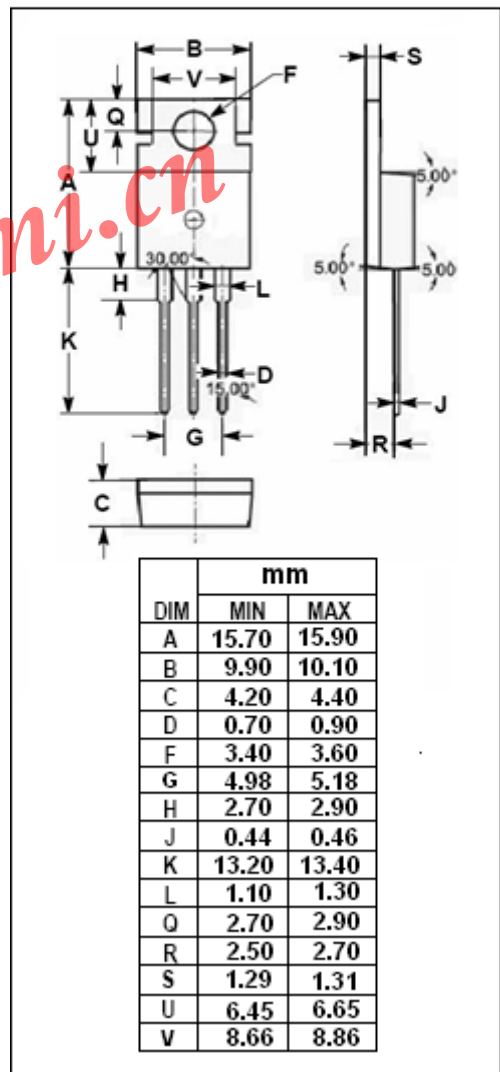
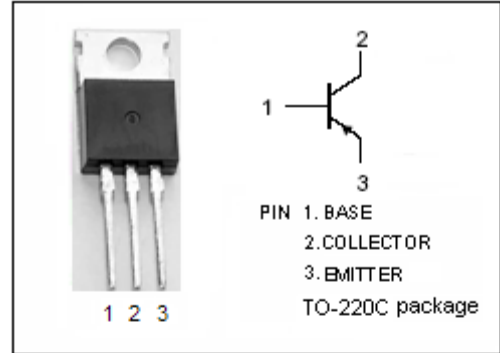
- High Collector Current: $I_C = -7A$
- Low Collector Saturation Voltage
: $V_{CE(sat)} = -0.5V(Max) @ I_C = -4A$
- Complement to Type 2SD1237

APPLICATIONS

- Designed for large current switching of relay drivers, high-speed inverters, converters applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-120	V
V_{CEO}	Collector-Emitter Voltage	-80	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current-Continuous	-7	A
I_{CM}	Collector Current-Peak	-12	A
P_C	Total Power Dissipation @ $T_C=25^\circ C$	40	W
	Total Power Dissipation @ $T_a=25^\circ C$	1.75	
T_J	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-55~150	$^\circ C$



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ELECTRICAL CHARACTERISTICS

 $T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -1\text{mA}; R_{BE} = \infty$	-80			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = -1\text{mA}; I_E = 0$	-120			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = -1\text{mA}; I_C = 0$	-6			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -4\text{A}; I_B = -0.4\text{A}$			-0.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB} = -80\text{V}; I_E = 0$			-0.1	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -4\text{V}; I_C = 0$			-0.1	mA
h_{FE-1}	DC Current Gain	$I_C = -1\text{A}; V_{CE} = -2\text{V}$	70		280	
h_{FE-2}	DC Current Gain	$I_C = -4\text{A}; V_{CE} = -2\text{V}$	30			
f_T	Current-Gain—Bandwidth Product	$I_C = -1\text{A}; V_{CE} = -5\text{V}$		20		MHz

Switching times

t_{on}	Turn-on Time	$R_L = 1.67\ \Omega, V_{CC} = -50\text{V}$ $I_C = -2\text{A}; I_{B1} = -I_{B2} = -0.2\text{A}$		0.2		μs
t_{stg}	Storage Time			0.7		μs
t_f	Fall Time			0.2		μs

◆ h_{FE-1} Classifications

Q	R	S
70-140	100-200	140-280